

20A, 200V SUPER-FAST RECOVERY RECTIFIER

GENERAL DESCRIPTION

SFR20S20ET(F) is a Super-Fast Recovery Diode, fabricated in advanced silicon planar epitaxial technology. The process parameter and the device structure are fine tuned with optimized performance of forward voltage drop and reverse recovery time.

Accuracy epitaxial dope control, advanced planar junction terminal structure and the platinum doped life control, guarantee the best overall performance, ruggedness and reliability characteristics.

SFR20S20ET is intended for use in the output rectification stage of SMPS, UPS, DC-DC converters as well as free-wheeling diode in low voltage inverters and chopper motor drivers.

FEATURES

- Ultrafast 25 Nanosecond Recovery Time
- Low Forward Voltage Drop
- Low reverse current leakage

ORDERING INFORMATION

$1 \circ 2$ $3 \circ 2$
22
TO-220HW-3L
1 ₂ TO-220F-3L

Part No.	Package	Marking	Hazardous Substance Control	Packing
SFR20S20ET	TO-220HW-3L	20S20ET	Pb free	Tube
SFR20S20EF	TO-220F-3L	20S20EF	Pb free	Tube



ABSOLUTE MAXIMUM RATINGS

Characteris	tics	Symbol	Rating	Unit
Peak Repetitive Reverse Vol	tage	V _{RRM}	200	V
Average Rectified Forward	Per Leg		10	٨
Current	Total Device	I _{F(AV)}	20	A
Peak Forward Surge	Derleg		150	٨
Current @8.3ms	Per Leg	IFSM	150	A
Operation Junction Tempera	ture Range	TJ	-55~+150	°C
Storage Temperature Range		T _{stg}	-55~+150	°C

THERMAL CHARACTERISTICS (PER LEG)

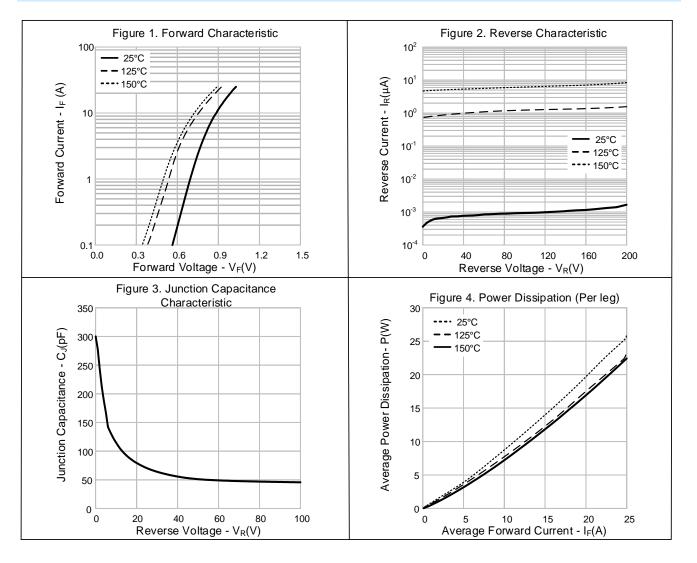
Characteristics	Symbol	Ratings	Unit
Thermal Resistance, Junction-to-Case (TO-220HW-3L)	$R_{ extsf{ heta}JC}$	1.5	°C/W
Thermal Resistance, Junction-to-Case (TO-220F-3L)	$R_{ extsf{ heta}JC}$	6.0	°C/W

ELECTRICAL CHARACTERISTICS (PER LEG)

Characteristics	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Maximum Forward	V _F	I _F =10Amps, T _C =25°C		0.89	1.0	V
Voltage	VF	I _F =10Amps, T _C =125°C		0.76	0.86	V
Maximum Reverse	1	Rated dc voltage, T _c =25°C			5.0	μA
Leakage Current	I _R	Rated dc voltage, T _C =125°C			50	μA
Maximum Reverse	+	I_F =0.5Amps, I_R =1.0Amps,		25		20
Recovery Time	t _{rr}	I _{REC} =0.25Amps		20		ns
Reverse Recovery Time	Trr	V _R =200V, I _F =10A, dI _F /dt=200.0A/µs		40		ns
Reverse Recovery	Qrr		-	66		nC
Charge						
Reverse Recovery				3.5		А
Current	Irrm			5.5		A

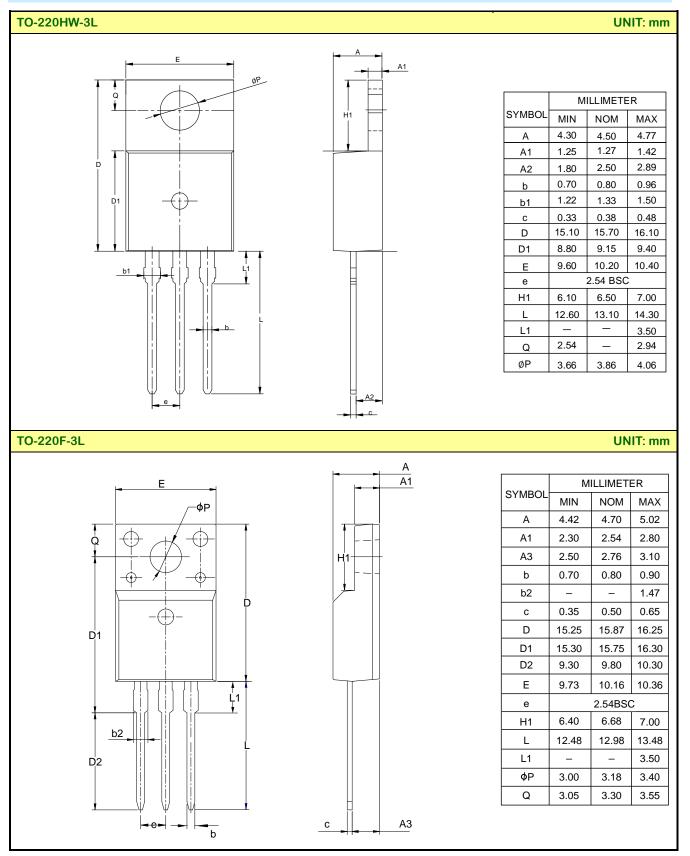


TYPICAL CHARACTERISTICS





PACKAGE OUTLINE







MOS DEVICES OPERATE NOTES:

Electrostatic charges may exist in many things. Please take following preventive measures to prevent effectively the MOS electric circuit as a result of the damage which is caused by discharge:

- The operator must put on wrist strap which should be earthed to against electrostatic.
- Equipment cases should be earthed.
- All tools used during assembly, including soldering tools and solder baths, must be earthed.
- MOS devices should be packed in antistatic/conductive containers for transportation.



Important notice :

- 1. Silan reserves the right to make changes of this instruction without notice.
- 2. Customers should obtain the latest relevant information when purchasing and should verify whether such information is latest and complete. Please read this instruction and application manual and related materials carefully before using products, including the circuit operation precautions, etc.
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- 8. Product promotion is endless, our company will wholeheartedly provide customers with better products!
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Part No	.: SFR20S20ET(F)	Document Type:	Datasheet	
Copyrig	ht: HANGZHOU SILAN MICROELECTRONICS	CO.,LTD Website:	http://www.silan.com.cn	
Rev.:	1.2			
Revisio	n History:			
1.	Modify the electrical diagram			
2.	Modify the important notice			
Rev.:	1.1			
Revisio	n History:			
1.	Add package of SFR20S20EF(TO-220F-3L)			
Rev.:	1.0			
Revisio	n History:			
1.	First release			